



10191/1614

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor : Richard SPITZ et al.
Serial No. : 09/720,720
Filed : February 28, 2001
For : METHOD FOR ELIMINATING DEFECTS IN SILICON
ELEMENTS THROUGH SELECTIVE ETCHING
Examiner : TRAN, Binh
Art Unit : 1765
Confirmation No. : 3872

Commissioner for Patents
Washington, D.C. 20231

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Jong H. Lee

AMENDMENT

SIR:

This Amendment addresses the Office Action mailed October 1, 2002, and it is respectfully requested that the above-identified application be amended as follows.

In the Claims:

Please cancel Claim 26. Please amend Claims 16, 17, 20, 21 and 29 as shown below:

16. (Amended) A method for substantially eliminating at least one of eruptions, impurities and damage in a crystal lattice, the method comprising the steps of:

providing a surface-plated, sawn-out part of a silicon wafer;

selectively drying the at least one silicon element by heating the at least one silicon element with a radiation heater in a vacuum at a pressure of less than about 0.1
atm; and